

isc Silicon NPN Power Transistor

2SC2168

DESCRIPTION

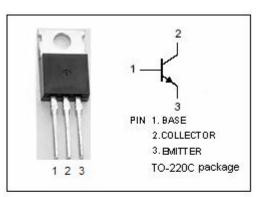
- Collector-Emitter Breakdown Voltage-: V_{(BR)CEO}= 200V(Min)
- DC Current Gain-
 - : h_{FE} = 60(Min)@ (V_{CE}= 10V, I_C= 0.7A)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

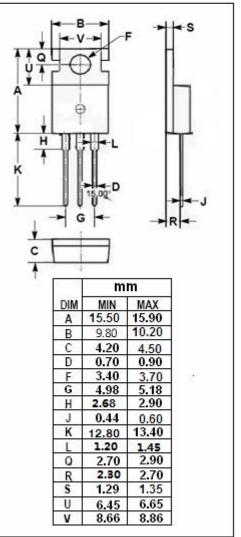
APPLICATIONS

• Designed for TV vertical output ,audio output driver and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|------------------------------------------------------|---------|------|--|
| V _{CBO} | Collector-Base Voltage | 200 | V | |
| V _{CEO} | Collector-Emitter Voltage | 200 | V | |
| V _{EBO} | Emitter-Base Voltage | 6 | V | |
| lc | Collector Current-Continuous | 2 | A | |
| lв | Base Current-Continuous | 1 | А | |
| Pc | Collector Power Dissipation @T _c =25°C | 30 | W | |
| TJ | Junction Temperature | 150 | °C | |
| T _{stg} | Storage Temperature | -55~150 | °C | |





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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|----------------------------------------------------|-----|------|-----|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 25mA; I _B = 0 | 200 | | | V |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C = 0.7A; I _B = 0.07A | | | 1.0 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 200V; I _E = 0 | | | 10 | μA |
| Іево | Emitter Cutoff Current | V _{EB} = 6V; I _C = 0 | | | 10 | μA |
| h _{FE} | DC Current Gain | I _C = 0.7A; V _{CE} = 10V | 60 | | | |
| Сов | Output Capacitance | I _E = 0; V _{CB} = 10V; f= 1МНz | | 35 | | pF |
| f⊤ | Current-Gain—Bandwidth Product | I _E = -0.2A ; V _{CE} = 12V | | 15 | | MHz |

Switching Times

| t _{on} | Turn-On Time | | 1.0 | μ S |
|------------------|--------------|-----------------------------------------------------------------------------------------------------------------|-----|------------|
| t _{stg} | Storage Time | I _C = 1A; I _{B1} = -I _{B2} = 0.1A; V _{CC} = 20V; R _L = 20 Ω | 3.0 | μ S |
| t _f | Fall Time | | 1.5 | μ S |

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